NSN 5961-01-094-5868

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Inclosure Material:

Metal

Overall Length:

Between 0.250 inches and 0.370 inches

Overall Diameter:

Between 0.470 inches and 0.500 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

90.0 breakdown voltage, collector-to-base, emitter open and 7.0 breakdown voltage, emitter-to-base, collector open and 90.0 breakdown voltage, collector to emitter, with specified voltage between base and emitter

Current Rating Per Characteristic:

Between 2.00 amperes source cutoff current and 4.00 amperes source cutoff current

Power Rating Per Characteristic:

29.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Test Data Document:

21101-76a0007 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

1 case and 2 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0